
2SC4913

Silicon NPN Triple Diffused

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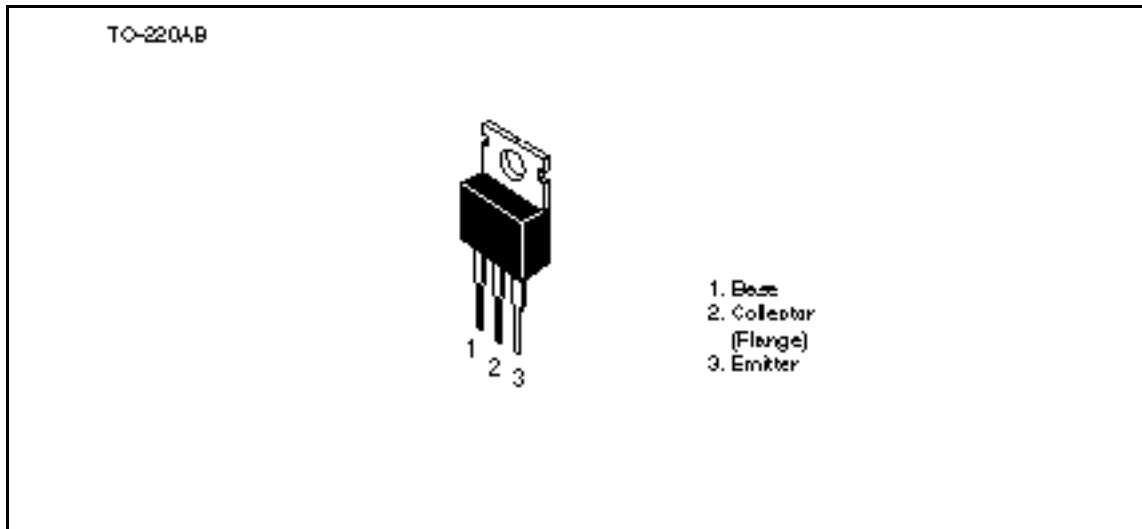
Application

High voltage amplifier

Features

- High breakdown voltage
- $V_{(BR)CEO} = 2000 \text{ V min}$

Outline



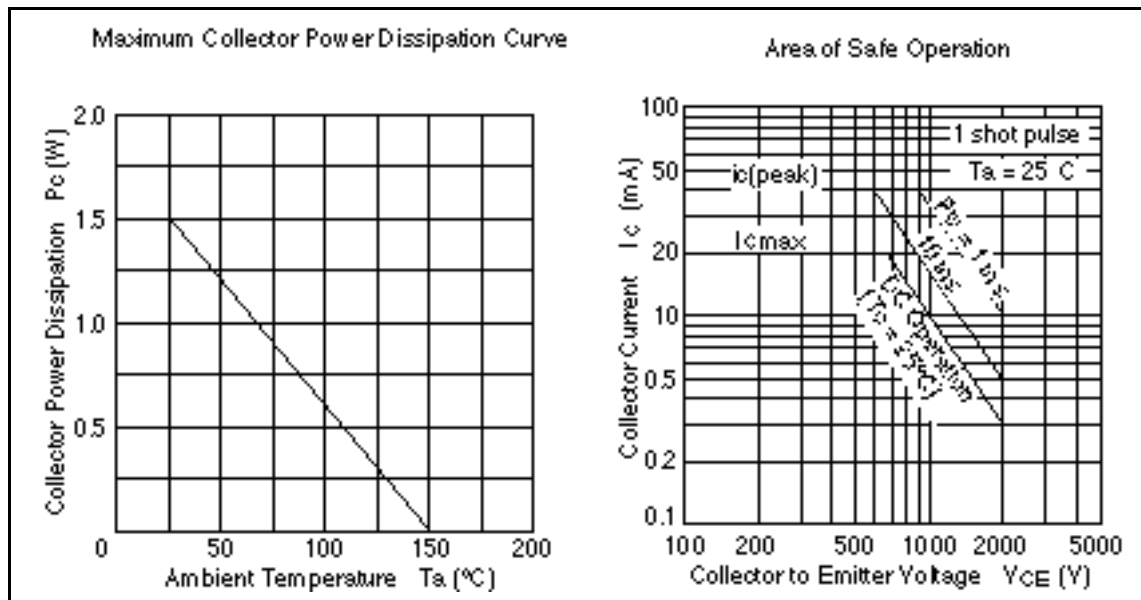
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Absolute Maximum Ratings (Ta = 25°C)

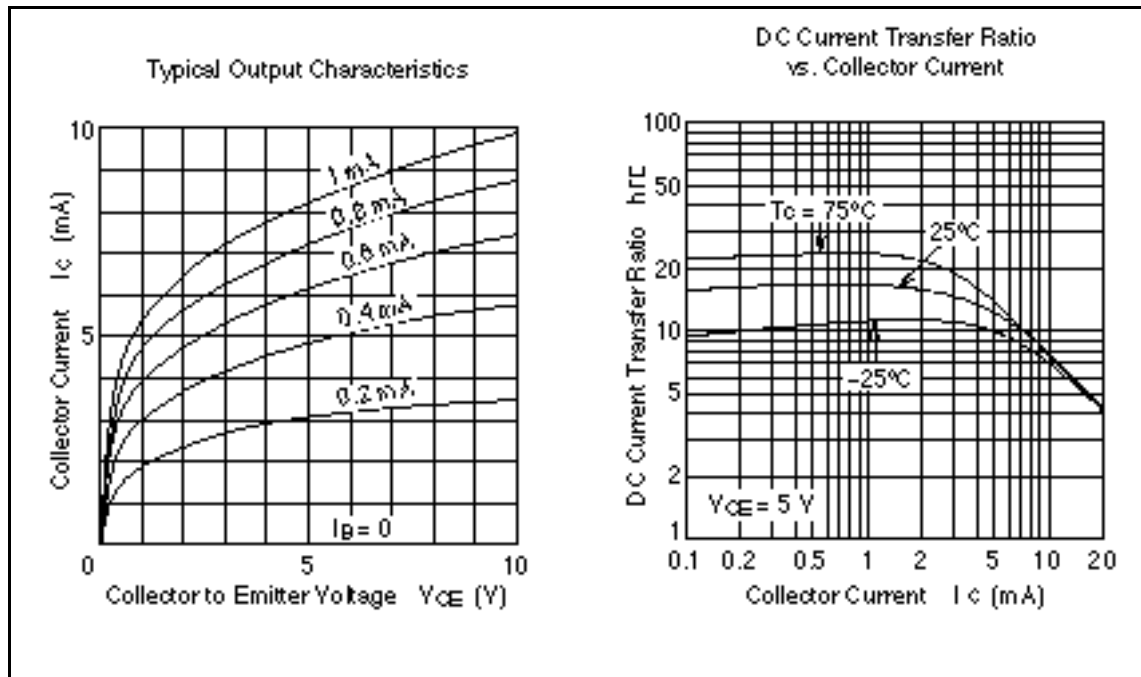
| Item | Symbol | Ratings | Unit |
|------------------------------|----------------------|-------------|------|
| Collector to base voltage | V_{CBO} | 2000 | V |
| Collector to emitter voltage | V_{CEO} | 2000 | V |
| Emitter to base voltage | V_{EBO} | 6 | V |
| Collector current | I_C | 20 | mA |
| Collector peak current | $I_{C(\text{peak})}$ | 40 | mA |
| Collector power dissipation | P_C | 1.5 | W |
| Junction temperature | T_j | 150 | °C |
| Storage temperature | T_{stg} | -55 to +150 | °C |

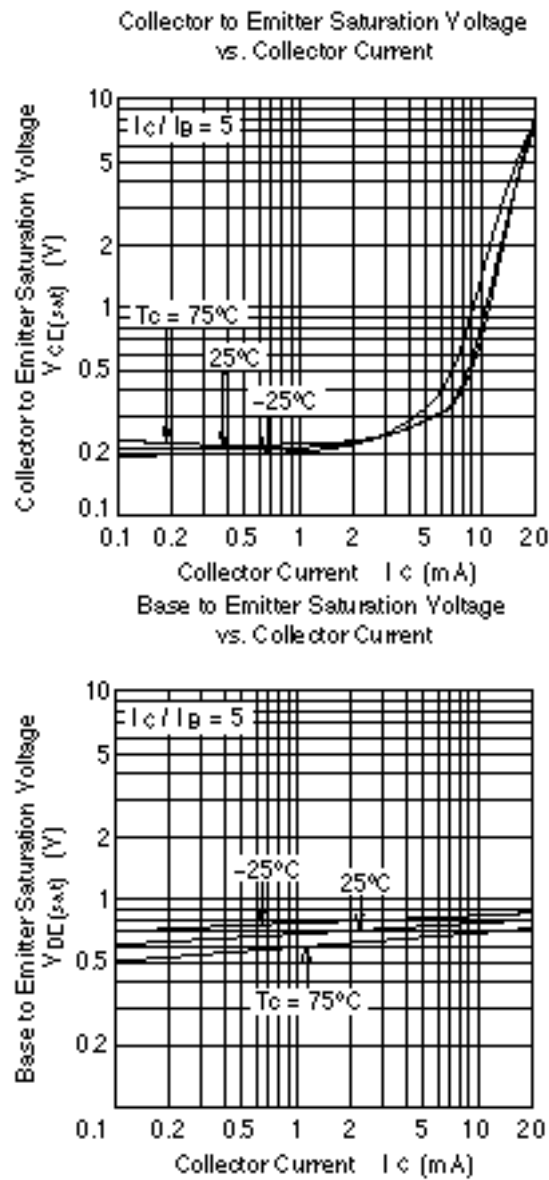
Electrical Characteristics (Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|---|----------------------|-----|-----|-----|---------------|--|
| Collector cutoff current | I_{CES} | — | — | 500 | μA | $V_{CE} = 2000 \text{ V}, R_{BE} = 0$ |
| Collector cutoff current | I_{CEO} | — | — | 5 | mA | $V_{CE} = 2000 \text{ V}, R_{BE} =$ |
| Emitter cutoff current | I_{EBO} | — | — | 500 | μA | $V_{EB} = 6 \text{ V}, I_C = 0$ |
| DC current transfer ratio | h_{FE} | 10 | — | — | | $V_{CE} = 5 \text{ V}, I_C = 1 \text{ mA}$ |
| Collector to emitter saturation voltage | $V_{CE(\text{sat})}$ | — | — | 5.0 | V | $I_C = 10 \text{ mA}, I_B = 2 \text{ mA}$ |

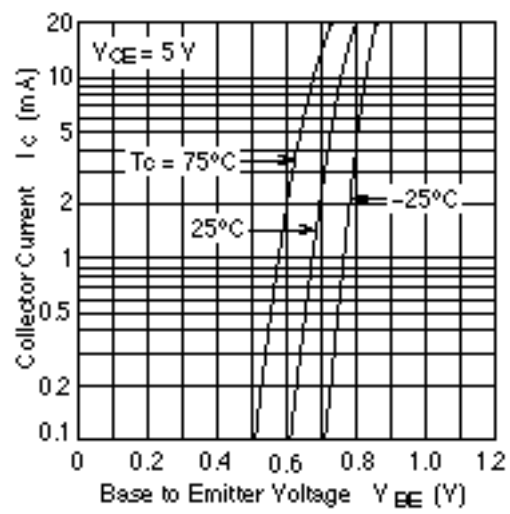


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Collector Current vs. Base to Emitter Voltage



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